

<b>Notice of References Cited</b>		Application No. <b>09/414,520</b>		Applicant(s) <b>Takahashi et al</b>	
		Examiner <b>Rudy Zervigon</b>		Group Art Unit <b>1763</b>	Page 1 of 1

  

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	DOCUMENT NO.	DATE	NAME		CLASS	SUBCLASS
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U	Hancock et al, "Time-Resolved Fourier transform infrared emission as a plasma diagnostic" J.Vac.Sci.Technol.A 13(6), Nov/Dec 1995, pp2945-2949	12/1995
V	Uhm et al, "A theoretical model of bulk plasma generated by the electron-cyclotron-resonance mechanism", Physics of Fluids B: Plasma Physics 5(6), June 1993, pp.1902-1910 <abstract>	6/1993
W	Etrillard et al, "Anisotropic etching of InP with low sidewall and surface induced damage in inductively coupled plasma etching using CF4", J.Vac.Sci.Technol.A 15(3), May/Jun 1997 pp.626-632	6/1997
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